



SamHop Microelectronics Corp.

# STS2308A

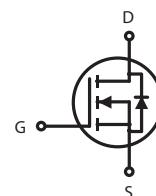
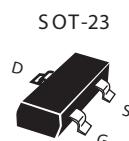
Dec 27 2004

## N-Channel Enhancement Mode Field Effect Transistor

PRODUCT SUMMARY		
V <sub>DSS</sub>	I <sub>D</sub>	R <sub>DSON</sub> (mΩ) Max
20V	2.7A	80 @ V <sub>GS</sub> = 4.5V 110 @ V <sub>GS</sub> = 2.5V

### FEATURES

- Super high dense cell design for low R<sub>DSON</sub>.
- Rugged and reliable.
- SOT-23 package.



ABSOLUTE MAXIMUM RATING (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	20	V
Gate-Source Voltage	V <sub>GS</sub>	±10	V
Drain Current-Continuous <sup>a</sup> @ T <sub>c</sub> =25°C -Pulsed <sup>b</sup>	I <sub>D</sub>	2.7	A
	I <sub>DM</sub>	10	A
Drain-Source Diode Forward Current <sup>a</sup>	I <sub>S</sub>	1.25	A
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	1.25	W
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to 150	°C

### THERMAL CHARACTERISTICS

Thermal Resistance, Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	100	°C/W
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ELECTRICAL CHARACTERISTICS (TA = 25 °C unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
<b>OFF CHARACTERISTICS</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250µA	20			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 16V, V <sub>GS</sub> = 0V		1		µA
Gate-Body Leakage	I <sub>GSS</sub>	V <sub>GS</sub> = ± 10V, V <sub>DS</sub> = 0V		±100		nA
<b>ON CHARACTERISTICS<sup>b</sup></b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250µA	0.5	0.8	1.5	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 2.7A		65	80	m-ohm
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 2A		90	110	m-ohm
On-State Drain Current	I <sub>D(ON)</sub>	V <sub>DS</sub> = 5V, V <sub>GS</sub> = 4.5V	6			A
Forward Transconductance	g <sub>Fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 2.7A		7		S
<b>DYNAMIC CHARACTERISTICS<sup>c</sup></b>						
Input Capacitance	C <sub>ISS</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V f = 1.0MHz		215		pF
Output Capacitance	C <sub>OSS</sub>			65		pF
Reverse Transfer Capacitance	C <sub>RSS</sub>			45		pF
<b>SWITCHING CHARACTERISTICS<sup>c</sup></b>						
Turn-On Delay Time	t <sub>D(ON)</sub>	V <sub>DD</sub> = 10V, I <sub>D</sub> = 1A, V <sub>GS</sub> = 4.5V, R <sub>GEN</sub> = 6 ohm		7.8		ns
Rise Time	t <sub>r</sub>			5.1		ns
Turn-Off Delay Time	t <sub>D(OFF)</sub>			11.6		ns
Fall Time	t <sub>f</sub>			9.3		ns
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, I <sub>D</sub> = 2.7A, V <sub>GS</sub> = 4.5V		3.8		nC
Gate-Source Charge	Q <sub>gs</sub>			1.2		nC
Gate-Drain Charge	Q <sub>gd</sub>			0.9		nC

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ELECTRICAL CHARACTERISTICS ( $T_A=25^\circ\text{C}$  unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ <sup>c</sup>	Max	Unit
DRAIN-SOURCE DIODE CHARACTERISTICS <sup>b</sup>						
Diode Forward Voltage	$V_{SD}$	$V_{GS} = 0V, I_S = 1.25A$		0.84	1.2	V

## Notes

- a. Surface Mounted on FR4 Board,  $t \leq 10\text{sec}$ .
- b. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
- c. Guaranteed by design, not subject to production testing.

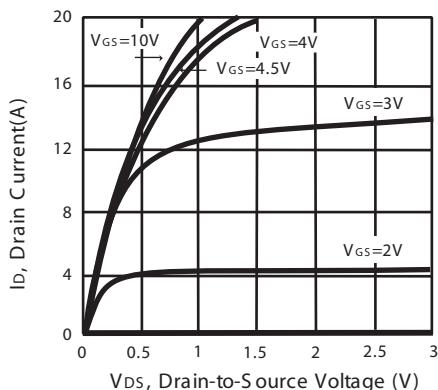


Figure 1. Output Characteristics

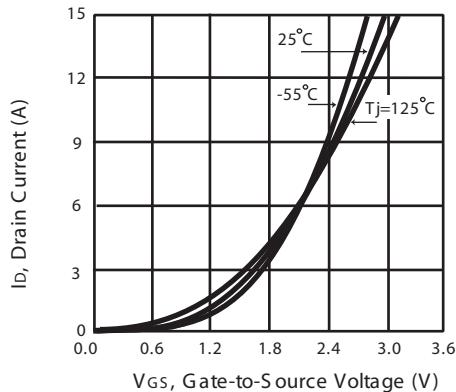


Figure 2. Transfer Characteristics

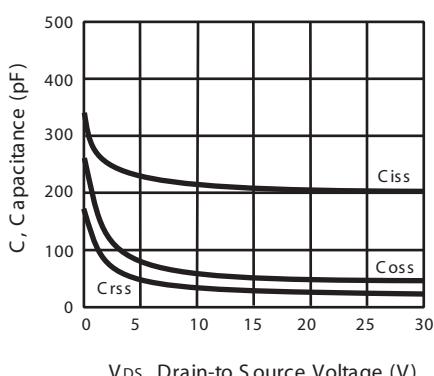


Figure 3. Capacitance

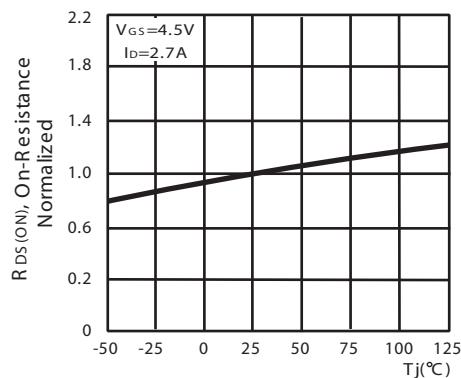
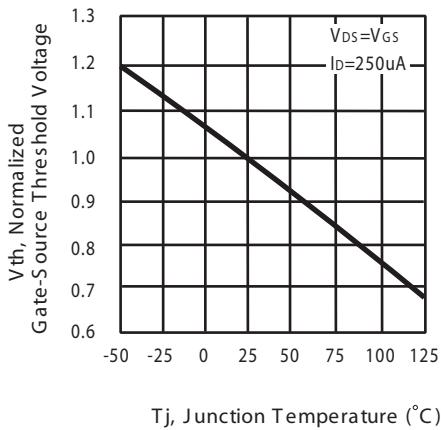
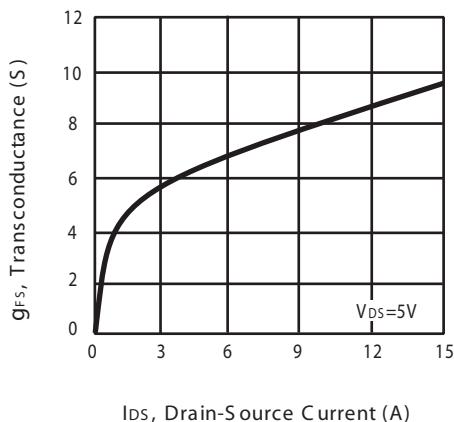


Figure 4. On-Resistance Variation with Temperature

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with Temperature



$I_{DS}$ , Drain-Source Current (A)

Figure 7. Transconductance Variation with Drain Current

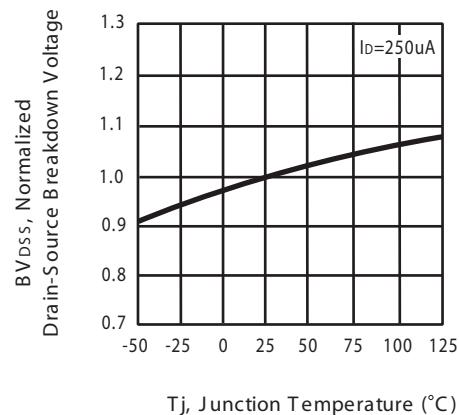
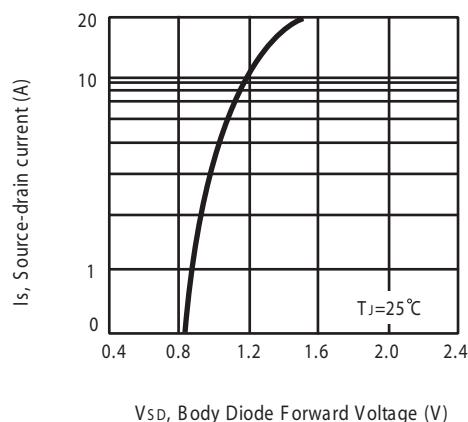
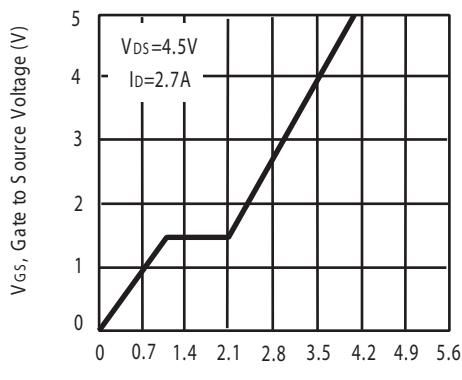


Figure 6. Breakdown Voltage Variation with Temperature



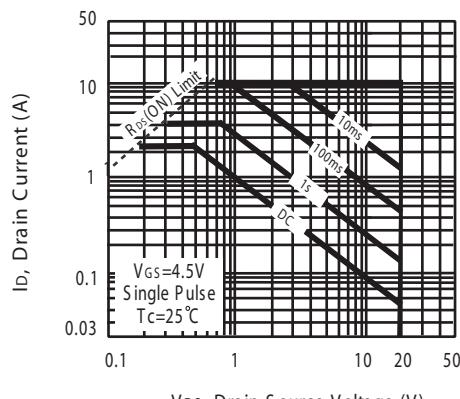
$V_{SD}$ , Body Diode Forward Voltage (V)

Figure 8. Body Diode Forward Voltage Variation with Source Current



$Q_g$ , Total Gate Charge (nC)

Figure 9. Gate Charge



$V_{DS}$ , Drain-Source Voltage (V)  
Figure 10. Maximum Safe Operating Area

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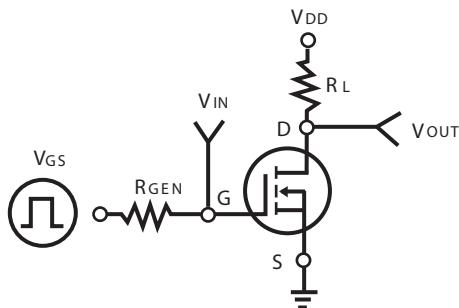


Figure 11. Switching Test Circuit

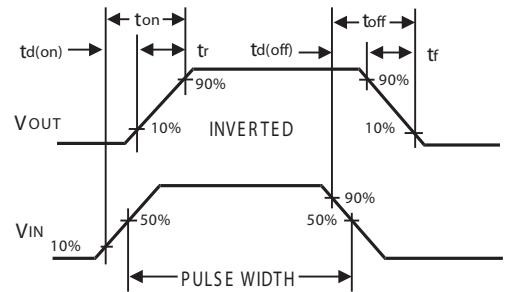
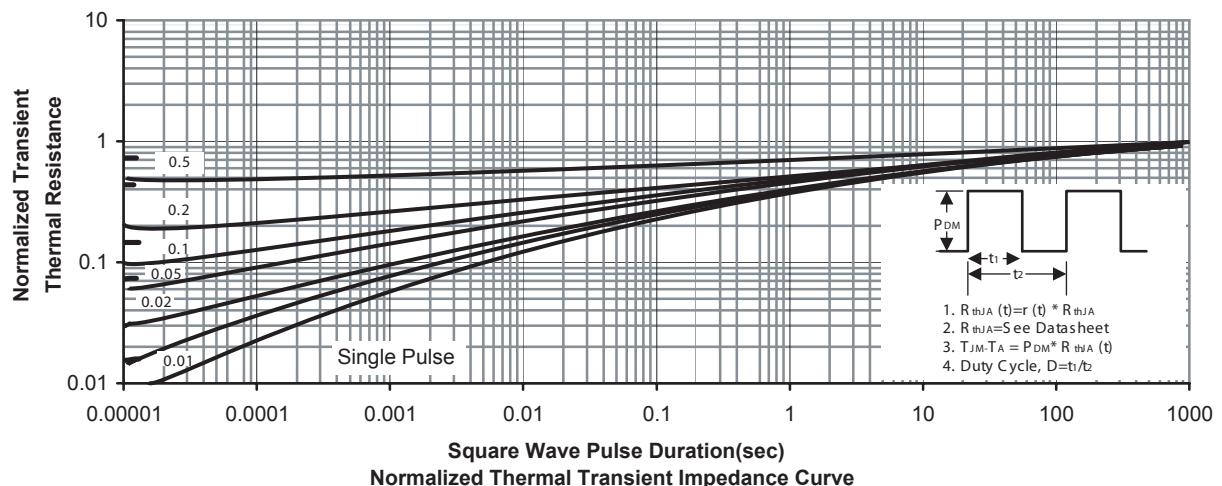


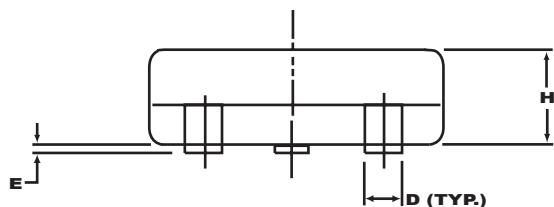
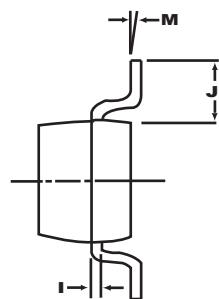
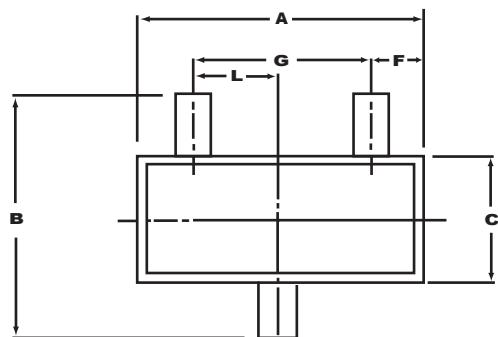
Figure 12. Switching Waveforms



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## PACKAGE OUTLINE DIMENSIONS

SOT-23

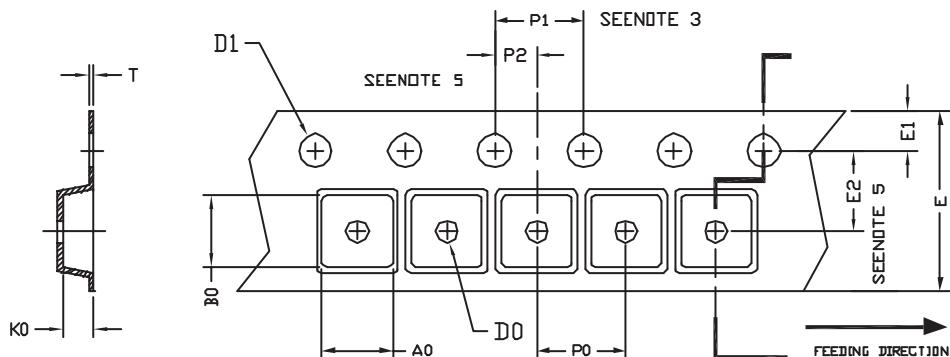


SYMBOLS	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	2.70	3.10	0.106	0.122
B	2.40	2.80	0.094	0.110
C	1.40	1.60	0.055	0.063
D	0.35	0.50	0.014	0.020
E	0	0.10	0	0.004
F	0.45	0.55	0.018	0.022
G	1.90 REF.		0.075 REF.	
H	1.00	1.30	0.039	0.051
I	0.10	0.20	0.004	0.008
J	0.40	-	0.016	-
L	0.45	1.15	0.033	0.045
M	0°	10°	0°	10°

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## SOT-23 Tape and Reel Data

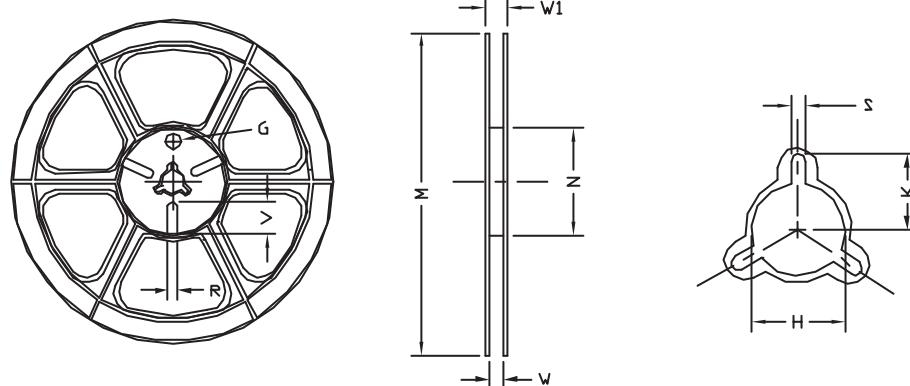
### SOT-23 Carrier Tape



UNIT:mm

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23	3.20 ±0.10	3.00 ±0.10	1.33 ±0.10	§ 1.00 +0.25	§ 1.50 +0.10	8.00 +0.30 -0.10	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.20 ±0.02

### SOT-23 Reel



UNIT:mm

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8mm	§ 178	§ 178 ±1	§ 60 ±1	9.00 ±0.5	12.00 ±0.5	§ 13.5 ±0.5	10.5	2.00 ±0.5	§ 10.0	5.00	18.00